

1.Description

The STD10NF10L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

This device is suitable for use as a Battery protection or in other Switching application.

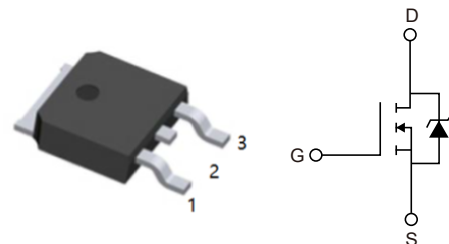
2.2Features

- Low Total Gate Charge
- Low Reverse Transfer Capacitance
- Improved dv/dt Capability
- Fast Switching Speed

4.Pinning information

Pin	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE

TO-252(DPAK)
top view



5.Absolute Maximum Ratings $T_A = 25^\circ\text{C}$

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Drain Current-Continuous	$T_C = 25^\circ\text{C}$	I_D	15	A
	$T_C = 100^\circ\text{C}$		10	
Drain Current-Pulsed ^{Note2}		I_{DM}	60	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	55	W
Storage Temperature Range		T_{STG}	-55 to 175	$^\circ\text{C}$
Junction Temperature Range		T_J	-55 to 175	$^\circ\text{C}$



6. Thermal Resistance Rating

Parameter	Symbol	Typ	Max	Units
Thermal Resistance, Junction-to-Case	R_{thJC}		2.72	°C/W

7. Specifications ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	μA
Gate-Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTIC						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1	1.6	3	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_{DS}=10A$		95	110	m Ω
		$V_{GS}=4.5V, I_{DS}=5A$		100	130	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{DS}=4A$	2			S
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1MHz$		632		pF
Output Capacitance	C_{oss}			37		pF
Reverse Transfer Capacitance	C_{rss}			21		pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=50V$ $R_L=2.8\Omega, R_{GEN}=6\Omega, I_D=10A$		12.6		ns
Rise Time	t_r			6		ns
Turn-Off Delay Time	$t_{D(off)}$			32.5		ns
Fall Time	t_f			4.3		ns
Total Gate Charge at 10V	Q_g	$V_{DS}=80V, I_{DS}=10A, V_{GS}=10V$		19.2		nC
Gate to Source Gate Charge	Q_{gs}			3.4		nC
Gate to Drain“Miller”Charge	Q_{gd}			6.1		nC



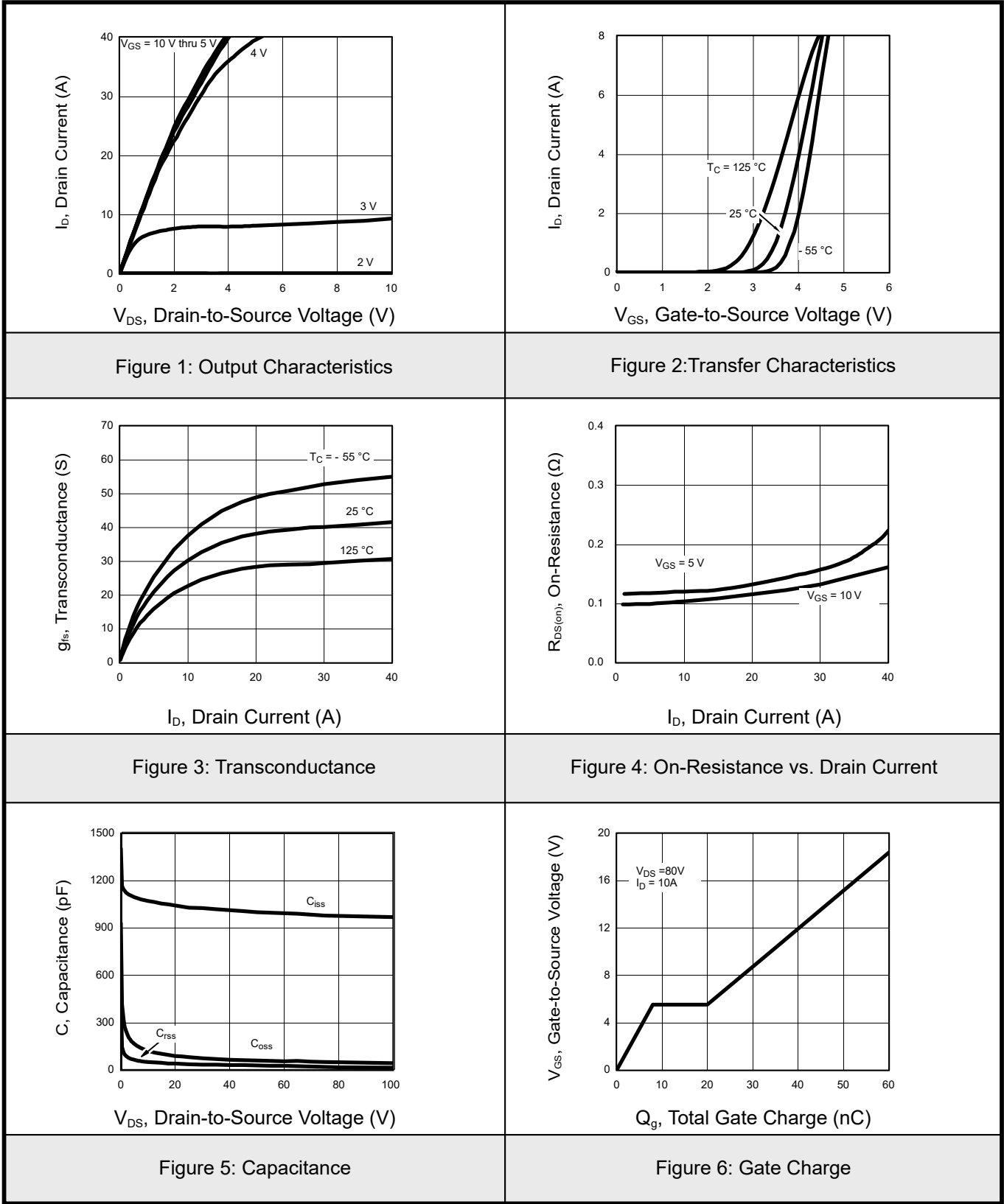
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{DS}=10A$			1.2	V

Notes:

- 1.The maximum current rating is package limited.
- 2.Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3.E_{AS} condition: T_J=25°C,V_{DD}=50V,V_G=10V, R_G=25Ω.



8.1 Typical Characteristic





8.2 Typical Characteristic

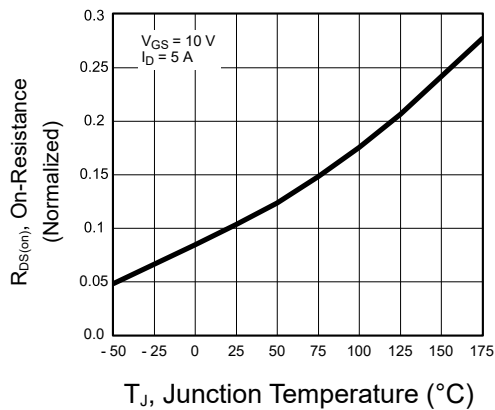


Figure 7: On-Resistance vs. Junction Temperature

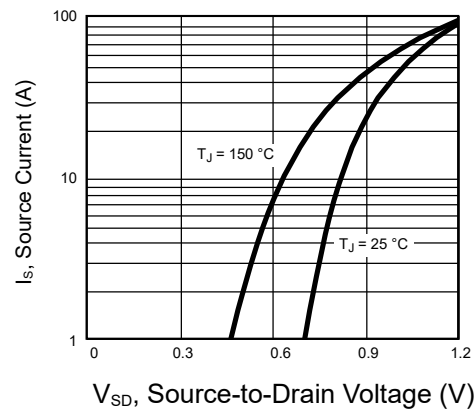


Figure 8: Source-Drain Diode Forward Voltage

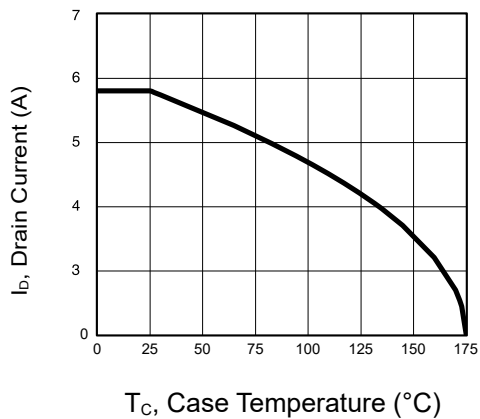
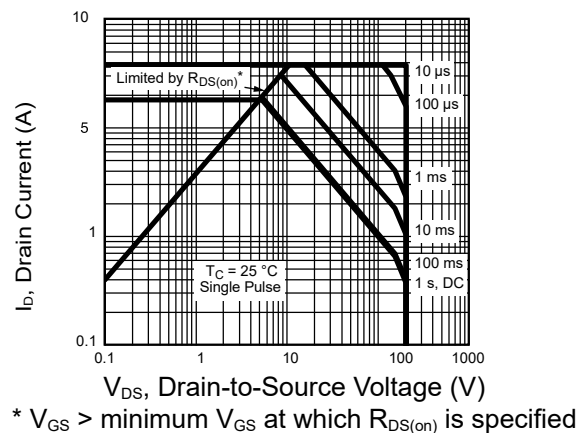


Figure 9: Maximum Avalanche Drain Current vs. Case Temperature



* $V_{GS} > \text{minimum } V_{GS} \text{ at which } R_{DS(on)} \text{ is specified}$

Figure 10: Safe Operating Area

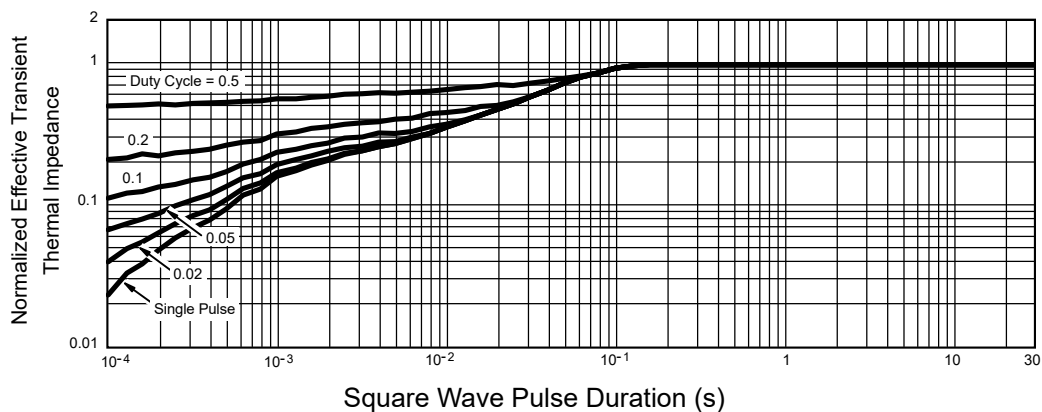


Figure 11: Normalized Thermal Transient Impedance, Junction-to-Case

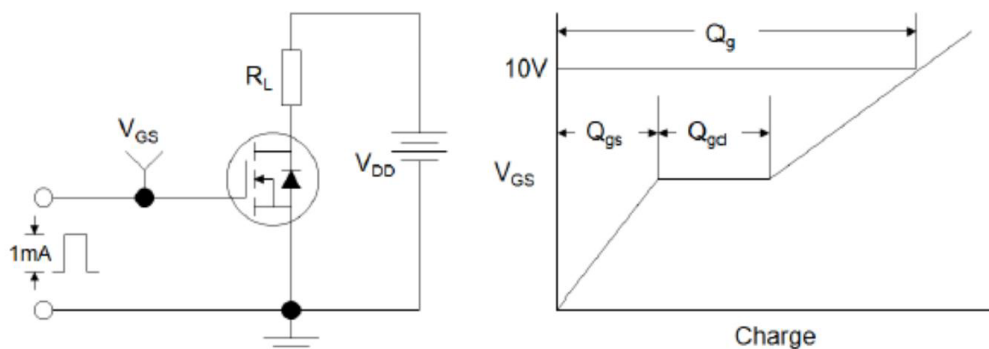


Figure1:Gate Charge Test Circuit & Waveform

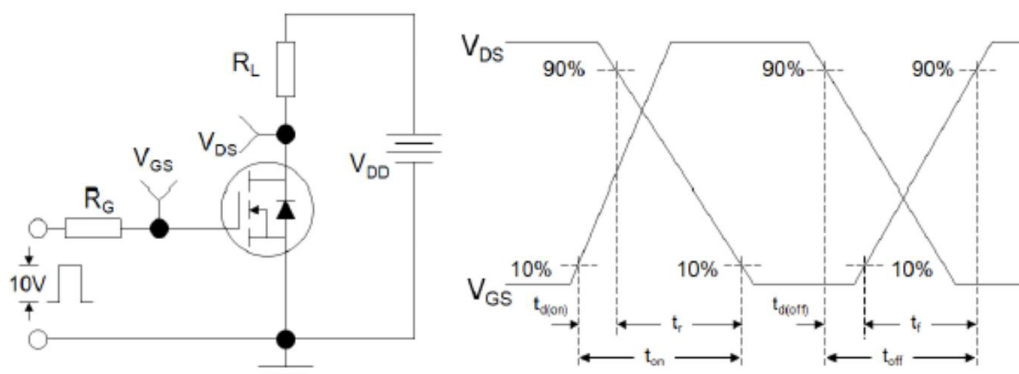


Figure 2: Resistive Switching Test Circuit & Waveforms

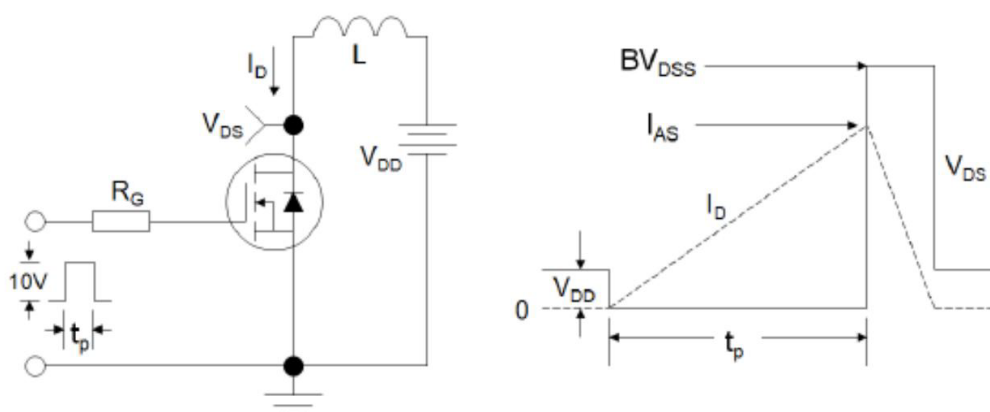


Figure 3:Unclamped inductive Switching Test Circuit & Waveforms

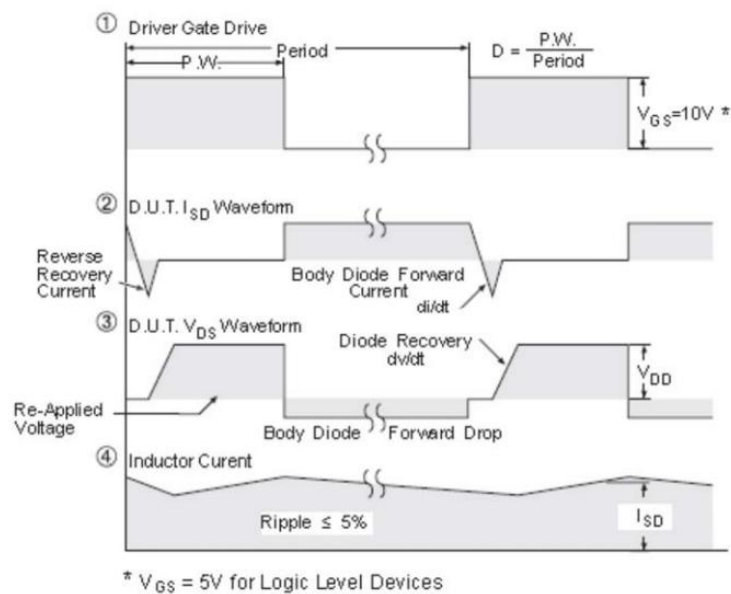
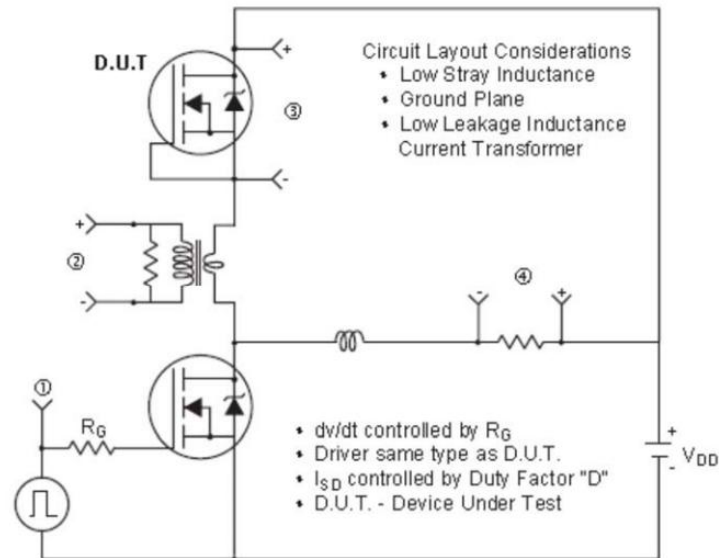
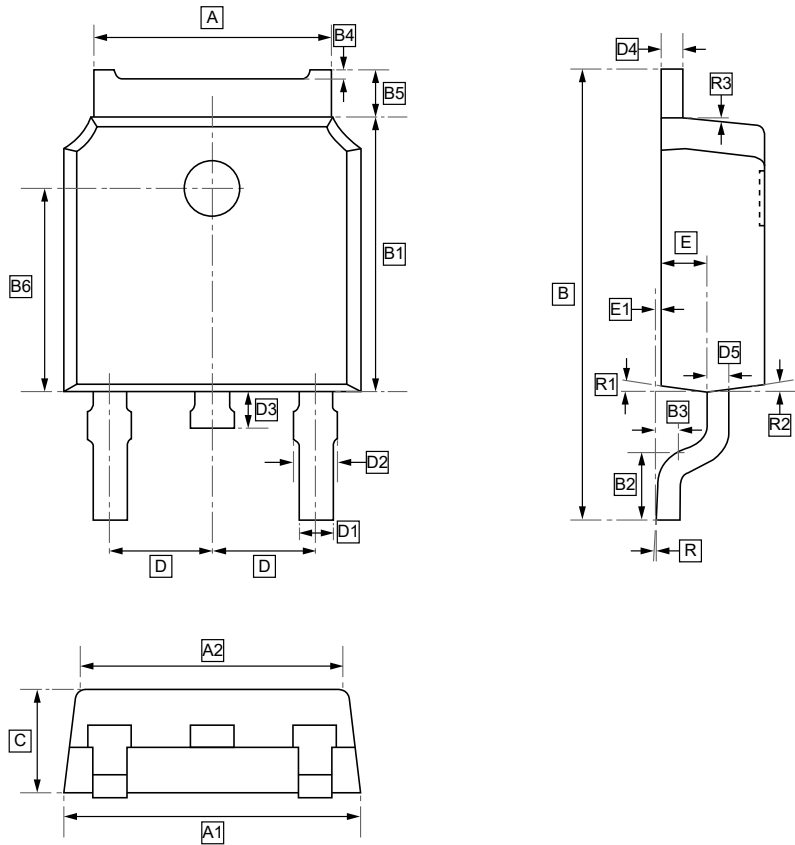


Figure 4: Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)



9.TO-252 Package Outline Dimensions



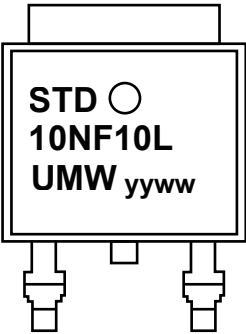
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	B	B1	B2	B3	B4	B5	B6	C	D
Min	5.1	6.4	5.6	9.5	5.9	1.35	0.4	0.1	0.85	4.35	2.15	2.286
Max	5.5	6.8	6.0	10.3	6.3	1.65	0.6	(typ.)	1.05	4.65	2.45	(typ.)

Symbol	D1	D2	D3	D4	D5	E	E1	R	R1	R2	R3
Min	0.66	0.81	0.65	0.42	0.42	0.86	0.05	0°	7°	7°	7°
Max	0.86	1.01	0.95	0.58	0.58	1.16	0.05	6°	(typ.)	(typ.)	(typ.)



10.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW STD10NF10L	TO-252	2500	Tape and reel



11.Disclaimer

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